

METHOD FOR CONTROLLING POLISHING WAFER

ABSTRACT OF THE INVENTION

[0036] A method for controlling polishing a wafer includes the following step. Firstly, a database storing a number of status data of a polished film of a wafer and a number of polishing parameters corresponding to the status data is established. Each of the polishing parameters includes a head sweep of a polishing head along a radial direction of a polishing platen. The head sweep refers to a movement distance range from a center of the polishing head to a center of the polishing platen during a polishing process. Subsequently, a first wafer having a predetermined status data is provided. Thereafter, the predetermined status data is compared with the status data in the database so as to find out the polishing parameter corresponding to the predetermined status data, thereby determining a first polishing parameter of the first wafer. Afterward, a first polishing process using the first polishing parameter is applied to the first wafer. The method can control the status of a polished film and optimize the polishing parameter.

Fig.2